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# N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A) <sup>a</sup>		
60	0.0049 at V <sub>GS</sub> = 10 V	60		

### **FEATURES**

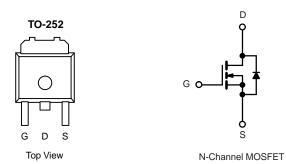


COMPLIANT

- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested

# **Applications**

- Synchronous Rectification in DC/DC and AC/DC Converters
- · Industrial and Motor Drive applications



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Gate-Source Voltage		$V_{GS}$	± 20	V		
Continuous Drain Current (T <sub>1</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	60			
Continuous Drain Current (1) = 175 °C)	T <sub>C</sub> = 100 °C		50 <sup>a</sup>			
Pulsed Drain Current		I <sub>DM</sub>	210	Α		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	60 <sup>a</sup>			
Avalanche Current		I <sub>AS</sub>	62	ı		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	125	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	146	W		
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	' D	12 <sup>b,c</sup>			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana lungtion to Ambienta	t ≤ 10 sec	D	13	20	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{thJA}$	35	50	°C/W
Maximum Junction-to-Case		R <sub>thJC</sub>	0.76	1.0	

#### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s}$ .





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<b>SPECIFICATIONS</b> ( $T_J = 25$	°C, unless o	otherwise noted)				,	
Parameter	Symbol	Test Conditions	Min.	Typ.a	Max.	Unit	
Static					1		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	-	3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
	I <sub>DSS</sub>	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50		
		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	65			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.0049	0.0059	Ω	
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C		0.0055	0.0068		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C		0.0063	0.0079		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A		0.0058	0.0075		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		80		S	
Dynamic							
Input Capacitance	C <sub>iss</sub>			10620		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		750			
Reverse Transfer Capacitance	C <sub>rss</sub>			85			
Total Gate Charge <sup>c</sup>	Qg			58	75	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		15			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			19			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			23			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 48 \text{ V}, R_{L} = 0.6 \Omega$ $I_{D} \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_{g} = 2.5 \Omega$		32		ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			28			
Fall Time <sup>c</sup>	t <sub>f</sub>			11			
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				210	Α	
Diode Forward Voltage	$V_{SD}$	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$		1		V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		31		ns	

### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

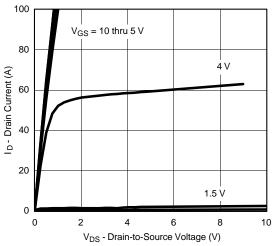


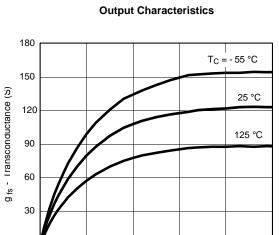
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10

### TYPICAL CHARACTERISTICS (25 °C unless noted)

# DTU3203 www.din-tek.jp





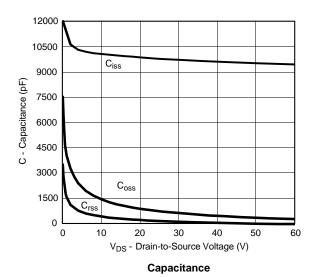
I<sub>D</sub> - Drain Current (A) **Transconductance** 

30

40

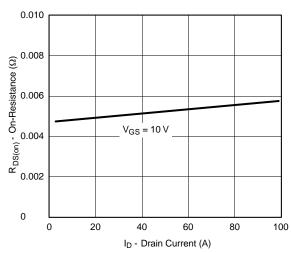
50

20

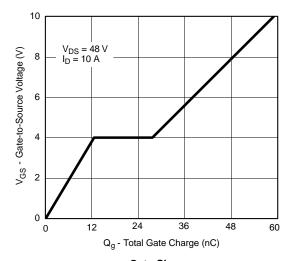


100 80 I<sub>D</sub> - Drain Current (A) 60 40 T<sub>C</sub> = 125 °C 20 25 °C 55 °C 0 0 2 V<sub>GS</sub> - Gate-to-Source Voltage (V)

**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 

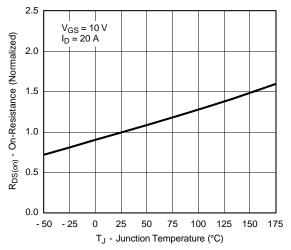


**Gate Charge** 

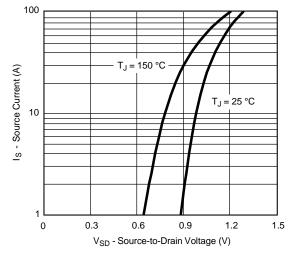




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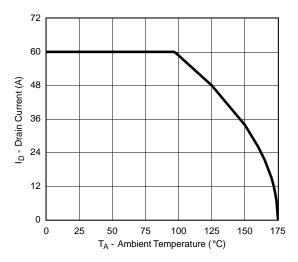
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

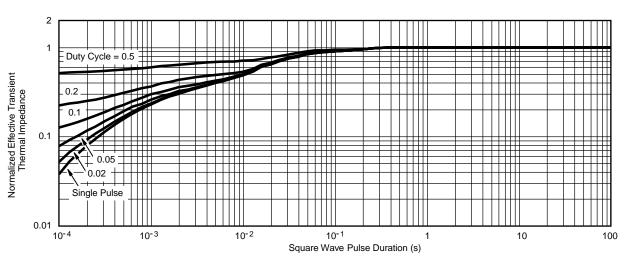


### THERMAL RATINGS



1000 Limited by 100 10 µs I<sub>D</sub> - Drain Current (A) 100 µs 10 1 ms 10 ms 100 ms DC T<sub>C</sub> = 25 °C Single Pulse 0.1 0.01 L 0.1 100  $V_{DS} - Drain-to-Source \ Voltage \ (V) \\ ^*V_{GS} > minimum \ V_{GS} \ at \ which \ R_{DS(on)} \ is \ specified$ Safe Operating Area

Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



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